

**April 2014** 

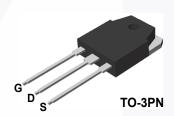
# FQA11N90C\_F109 N-Channel QFET® MOSFET 900 V, 11.0 A, 1.1 $\Omega$

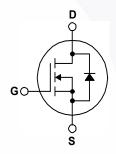
#### **Features**

- 11 A, 900 V,  $R_{DS(on)} = 1.1 \Omega$  (Max.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 5.5 \text{ A}$
- Low Gate Charge (Typ. 60 nC)
- · Low Crss (Typ. 23 pF)
- 100% Avalanche Tested
- · RoHS compliant

### **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.





### **MOSFET Maximum Ratings** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter			FQA11N90C_F109	Unit
$V_{DSS}$	Drain to Source Voltage			900	V
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25°C)	- Continuous (T <sub>C</sub> = 25°C)		Α
	Drain Current	- Continuous (T <sub>C</sub> = 100°C)		6.9	Α
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	44.0	Α
$V_{GSS}$	Gate to Source Voltage			± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy		(Note 2)	960	mJ
I <sub>AR</sub>	Avalanche Current		(Note 1)	11.0	Α
E <sub>AR</sub>	Repetitive Avalanche Energy		(Note 1)	30	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	4.0	V/ns
$P_{D}$	Dower Dissinction	(T <sub>C</sub> = 25°C)		300	W
	Power Dissipation	- Derate Above 25°C		2.38	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C

### **Thermal Characteristics**

Symbol	Parameter	FQA11N90C_F109	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.42	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max	40	°C/W

### **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA11N90C_F109	FQA11N90C	TO-3PN	Tube	N/A	N/A	30 units

### **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	900			V
$\Delta BV_{DSS}$ / $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		1.02		V/°C
	Zana Oata Valtana Basin Ourset	V <sub>DS</sub> = 900 V, V <sub>GS</sub> = 0 V			10	μΑ
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 720 V, T <sub>C</sub> = 125°C			100	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5.5 A		0.91	1.1	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 5.5 A	-	9.0		S
Dynami	ic Characteristics					
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,	\	2530	3290	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		215	280	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			23	30	pF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 450 V, I <sub>D</sub> = 11.0 A,		60	130	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		130	270	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			130	270	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		85	180	ns
$Q_g$	Total Gate Charge	V <sub>DS</sub> = 720 V, I <sub>D</sub> = 11.0 A,	/	60	80	nC
$Q_{gs}$	Gate-Source Charge	V <sub>GS</sub> = 10 V		13		nC
$Q_{gd}$	Gate-Drain Charge	(Note 4)		25		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
Is	Maximum Continuous Drain-Source Diode Forward Current				11.0	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				44.0	Α
$V_{SD}$	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 11.0 A			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 11.0 A,		1000		ns
Q <sub>rr</sub>	Reverse Recovery Charge			17.0		μС

#### Notes:

<sup>1.</sup> Repetitive rating : pulse width limited by maximum junction temperature.

<sup>2.</sup> L = 15 mH, I<sub>AS</sub> = 11.0 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C.

<sup>3.</sup>  $I_{SD} \le$  11.0 A, di/dt  $\le$  200 A/ $\mu$ s,  $V_{DD} \le$  BV $_{DSS}$ , starting  $T_J$  = 25°C.

<sup>4.</sup> Essentially independent of operating temperature.

### **Typical Characteristics**

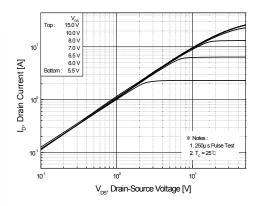


Figure 1. On-Region Characteristics

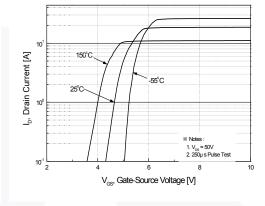


Figure 2. Transfer Characteristics

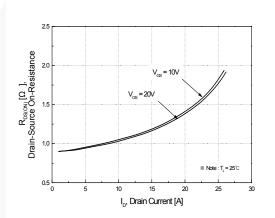


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

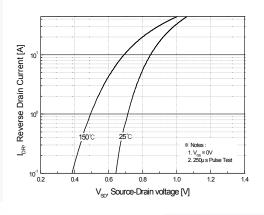


Figure 4. Body Diode Forward Voltage Variation with Source Current

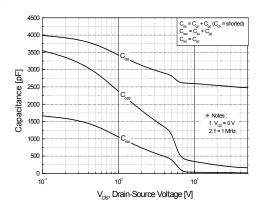


Figure 5. Capacitance Characteristics

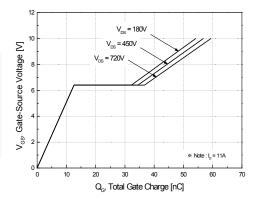
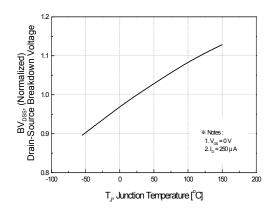


Figure 6. Gate Charge Characteristics

### Typical Characteristics (Continued)



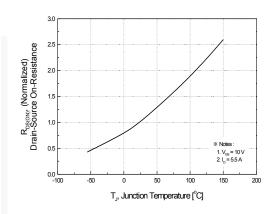
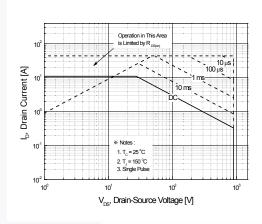


Figure 7. Breakdown Voltage Variation

Figure 8. On-Resistance Variation



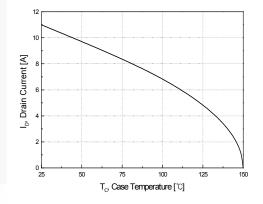


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs Case Temperature

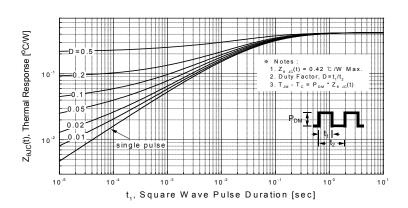


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

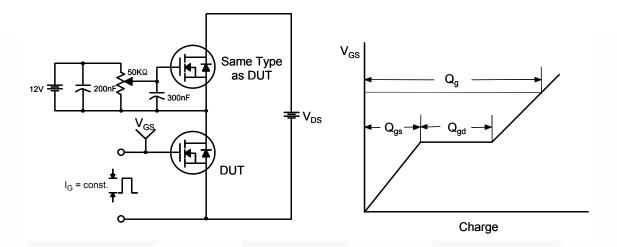


Figure 13. Resistive Switching Test Circuit & Waveforms

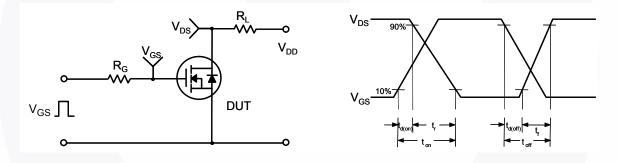
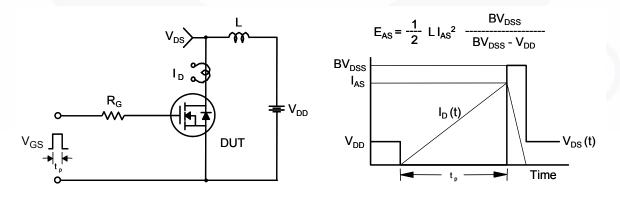


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



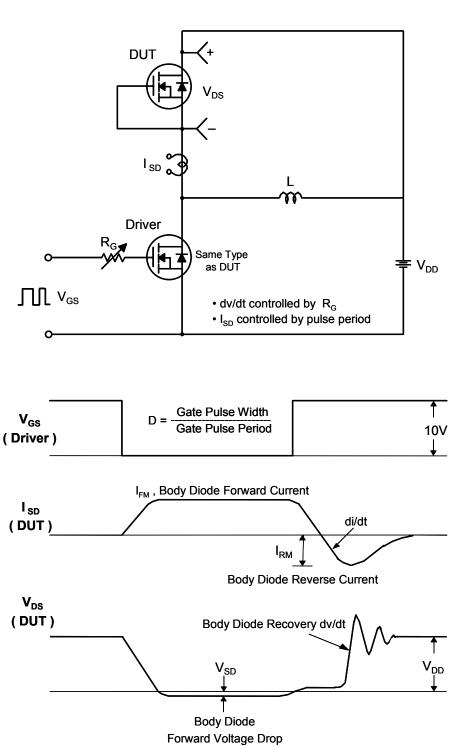
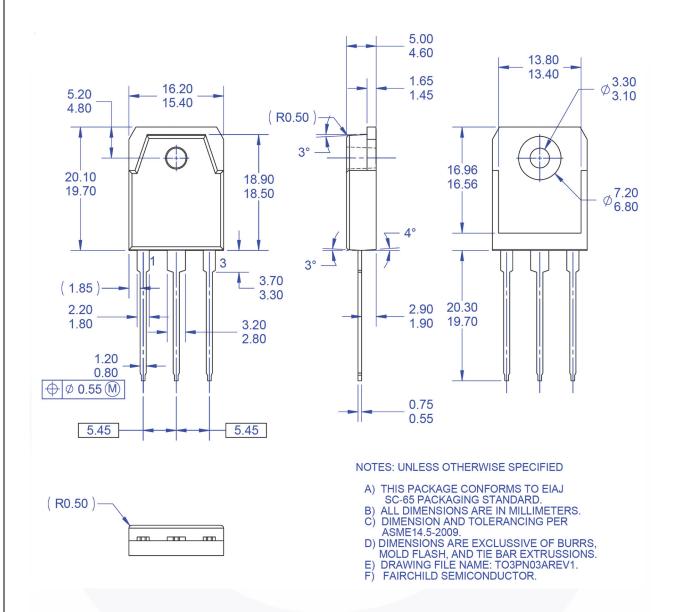


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

### **Mechanical Dimensions**



### Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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